

said capacitor, remains within a range of design margin of said nonvolatile semiconductor storage device at a coercive electric field value at a specified temperature.]

5. (Once Amended) [The] A nonvolatile semiconductor storage device [according to claim 1, wherein] comprising:

[said capacitor comprises] a complex capacitor comprised of a dielectric thin film having a temperature dependency, in which a dielectric constant of the capacitor decreases [accompanying] an increase in temperature in [the] an operational [guaranteed] temperature range of said nonvolatile semiconductor storage device, and a ferroelectric capacitor provided [with the] having a ferroelectric thin film [serially connected therebetween].

6. (Once Amended) The nonvolatile semiconductor storage device according to claim 5, wherein:

    said complex capacitor comprises a complex thin film [showing] having a ferroelectric property rendered by a compounding action of the dielectric thin film having [the] a temperature dependency wherein the dielectric constant decreases accompanying [the] an increase in temperature in the operational [guaranteed] temperature range of said nonvolatile semiconductor storage device, the ferroelectric thin film exhibiting the ferroelectric property in the operational [guaranteed] temperature range, and a conductive thin film held between said dielectric thin film and said ferroelectric thin film.

7. (Once Amended) The nonvolatile semiconductor storage device according to claim 5, wherein:

    said dielectric thin film has the temperature dependency in which the dielectric constant decreases accompanying [the] an increase in temperature in the operational